



Fig.	V <sub>CE</sub> V	I <sub>C</sub> A	T <sub>C</sub> = 25°C A	V <sub>CE</sub> (sat) max. V	Digi-Key Part No.	Price Each	IXYS Part No.
1							
10							
50							
<b>IGBTs — Insulated Gate Bipolar Transistors — High Speed</b>							
12	600	48	2.7	2.5	IXGH24N60A-ND	8.61 7.18 5.74	IXGH24N60A
	600	75	2.7	2.5	IXGH50N60A-ND	17.01 15.39 13.66	IXGH50N60A
	600	48	2.5	2.5	IXGH24N60B-ND	6.03 5.46 4.76	IXGH24N60B
	600	48	2.5	2.5	IXGH24N60C-ND	6.24 5.65 4.93	IXGH24N60C
	600	60	2.5	2.5	IXGH32N60C-ND	7.33 6.64 5.79	IXGH32N60C
	600	75	2.5	2.5	IXGH50N60B-ND	11.53 10.44 9.12	IXGH50N60B
	600	75	3.0	3.0	IXSH40N60A-ND	13.29 11.08 7.35	IXSH40N60A
<b>IGBTs — Insulated Gate Bipolar Transistors with Diode, Combi Pack — low V<sub>CE</sub> (sat)</b>							
12	1000	20	3.5	3.5	IXGH10N100U1-ND	11.66 10.55 9.37	IXGH10N100U1
	1000	34	3.5	3.5	IXGH17N100U1-ND	11.91 10.78 9.57	IXGH17N100U1
	1700	25	3.3	3.3	IXBH16N170-ND	16.47 13.73 9.12	IXBH16N170
	600	60	2.3	2.3	IXGH32N60B1-ND	12.96 10.80 7.16	IXGH32N60B1
13	600	75	3.0	3.0	IXGM40N60A-ND	39.87 33.23 26.58	IXGM40N60A
<b>IGBTs — Insulated Gate Bipolar Transistors with Diode, Combi Pack — High Speed</b>							
12	600	48	2.7	2.5	IXGH24N60AU1-ND	9.49 8.59 7.63	IXGH24N60AU1
	600	60	1.8	1.8	IXGH30N60BD1-ND	10.77 9.75 8.52	IXGH30N60BD1
	600	60	2.5	2.5	IXGH32N60CD1-ND	9.26 8.38 7.32	IXGH32N60CD1
	600	55	2.5	2.5	IXSH30N60CD1-ND	11.09 10.04 8.77	IXSH30N60CD1
	1000	20	4.0	4.0	IXGH10N100AU1-ND	11.30 10.23 9.09	IXGH10N100AU1
	1000	34	4.0	4.0	IXGH17N100AU1-ND	12.08 10.93 9.71	IXGH17N100AU1
<b>IGBT High Speed With Diode — RoHS Compliant</b>							
12	600	20	2.5	2.5	IXSH10N60B2D1-ND	3.02 2.74 2.45	IXSH10N60B2D1
	600	35	2.5	2.5	IXSH20N60B2D1-ND	4.28 3.88 3.47	IXSH20N60B2D1
	600	48	2.5	2.5	IXSH30N60B2D1-ND	5.52 5.00 4.48	IXSH30N60B2D1
14	600	20	2.5	2.5	IXSA10N60B2D1-ND	2.46 2.23 1.99	IXSA10N60B2D1
	600	35	2.5	2.5	IXSA20N60B2D1-ND	3.76 3.41 3.05	IXSA20N60B2D1
15	600	20	2.5	2.5	IXSP10N60B2D1-ND	2.42 2.19 1.96	IXSP10N60B2D1
	600	35	2.5	2.5	IXSP20N60B2D1-ND	3.72 3.37 3.01	IXSP20N60B2D1
16	600	20	2.5	2.5	IXSQ10N60B2D1-ND	2.71 2.46 2.20	IXSQ10N60B2D1
	600	35	2.5	2.5	IXSQ20N60B2D1-ND	3.99 3.61 3.23	IXSQ20N60B2D1
17	600	48	2.5	2.5	IXST30N60B2D1-ND	6.55 5.93 5.31	IXST30N60B2D1
	1700	75	3.3	3.3	IXGT32N170CT-ND†	16.49 12.98 11.76	IXGT32N170 T&R
	1700	75	3.3	3.3	IXGT32N170TR-ND‡	4261.20/400	IXGT32N170 T&R

Fig.	V <sub>DRM</sub> V	I <sub>TAV</sub> A	T <sub>C</sub> = 85°C A	I <sub>T</sub> RMS A	Digi-Key Part No.	Price Each	IXYS Part No.
1							
10							
50							
<b>Phase Control SCRs</b>							
18	800	16	16	25	CS8-08102-ND	14.07 11.73 7.04	CS8-08102
	1200	16	16	25	CS8-12102-ND	14.76 12.30 7.39	CS8-12102
19	800	25	50	50	CS23-08102-ND	22.62 18.85 11.31	CS23-08102
	1200	25	50	50	CS23-12102-ND	23.73 19.78 11.87	CS23-12102
20	800	63	120	120	CS35-08104-ND	29.79 24.83 14.89	CS35-08104
	1200	63	120	120	CS35-12104-ND	31.26 26.05 15.63	CS35-12104
	1400	63	120	120	CS35-14104-ND	32.76 27.30 16.38	CS35-14104

Fig.	V <sub>DRM</sub> VA	I <sub>TAV</sub> @ T <sub>C</sub> A	I <sub>T</sub> RMS A	Digi-Key Part No.	Price Each	IXYS Part No.
1						
10						
50						
<b>SCR Module — RoHS Compliant</b>						
1B	1200	2x116	85	2x180	MCC95-12101B-ND	69.63 58.03 34.81
	1600	116	85	180	MCC95-16108B-ND	73.71 61.43 36.85
	1600	2x32	85	2x50	MCC26-16101B-ND	47.85 39.88 23.92
1C	1600	2x116	85	2x180	MCC95-16101B-ND	76.26 63.55 38.12
21	1600	2x190	85	2x300	MCC162-16101-ND	141.96 118.30 70.99

Fig.	V <sub>DSS</sub> max. V	I <sub>D25</sub> A	R <sub>DS(on)</sub> Ω	Digi-Key Part No.	Price Each	IXYS Part No.
1						
10						
50						
<b>MOSFETs — N-Channel Enhancement Mode — RoHS Compliant</b>						
22	200	50	.045	IXFM50N20-ND	23.46 19.55 15.65	IXFM50N20
23	500	14	0.4	IRFP450X-ND	4.49 4.07 3.56	IRFP450
<b>MOSFETs — P-Channel Enhancement Mode — RoHS Compliant</b>						
23	-200	-24	1.1	IXTH24P20-ND	9.84 8.20 5.45	IXTH24P20
	-600	-10	1.0	IXTH10P60-ND	10.80 9.00 5.98	IXTH10P60
<b>MegaMOSFET™ — N-Channel Enhancement Mode — High Voltage — RoHS Compliant</b>						
23	1100	13	0.920	IXTH13N110-ND	17.58 15.91 13.89	IXTH13N110
<b>MegaMOSFET™ N-Channel Enhancement Mode — RoHS Compliant</b>						
23	500	20	0.27	IRFP460X-ND	6.15 5.57 4.86	IRFP460
	600	20	0.35	IXTH20N60-ND	10.42 9.43 8.23	IXTH20N60

Fig.	V <sub>DSS</sub> max. V	I <sub>D25</sub> A	R <sub>DS(on)</sub> Ω	Digi-Key Part No.	Price Each	IXYS Part No.
1						
10						
50						
<b>MOSFETs — P-Channel Enhancement Mode Avalanche Rated</b>						
23	-500	-7	1.500	IXTH7P50-ND	9.16 8.29 7.24	IXTH7P50
	-500	-8	1.200	IXTH8P50-ND	5.40 4.89 4.27	IXTH8P50
	-500	-10	0.900	IXTH10P50-ND	11.19 10.13 8.85	IXTH10P50
	-500	-11	0.750	IXTH11P50-ND	10.29 8.58 6.86	IXTH11P50
<b>MOSFETs — N-Channel Enhancement Mode with Fast Intrinsic Diode</b>						
23	70	76	0.011	IXFH76N07-11-ND	8.19 7.41 6.47	IXFH76N07-11
	70	76	0.012	IXFH76N07-12-ND	7.79 7.05 6.15	IXFH76N07-12
	100	80	0.015	IXFH80N100-ND	11.55 10.45 9.13	IXFH80N100
	200	42	0.06	IXFH42N20-ND	13.50 12.22 10.85	IXFH42N20
	200	50	0.045	IXFH50N20-ND	8.19 7.41 6.47	IXFH50N20
	200	58	0.04	IXFH58N20-ND	8.55 7.74 6.76	IXFH58N20
	200	58	0.040	IXFH58N20Q-ND	8.55 7.74 6.76	IXFH58N20Q
	200	80	0.028	IXFH80N20Q-ND	12.33 11.16 9.74	IXFH80N20Q
	300	40	0.085	IXFH40N30-ND	8.36 7.57 6.61	IXFH40N30
	300	40	0.08	IXFH40N30Q-ND	8.36 7.57 6.61	IXFH40N30Q
	300	40	0.085	IXTH40N30-ND	10.77 9.75 8.52	IXTH40N30
	300	52	0.060	IXFH52N30Q-ND	12.71 11.50 10.04	IXFH52N30Q
	500	13	0.4	IXFH13N50-ND	4.56 4.13 3.62	IXFH13N50
	500	21	0.25	IXFH21N50-ND	7.25 6.56 5.83	IXFH21N50
	500	24	0.23	IXFH24N50-ND	7.94 7.19 6.27	IXFH24N50
	500	26	0.20	IXFH26N50-ND	8.38 7.59 6.62	IXFH26N50
	500	26	0.20	IXFH26N50Q-ND	8.38 7.59 6.62	IXFH26N50Q
	500	32	0.15	IXFH32N50-ND	13.61 12.32 10.76	IXFH32N50
	600	20	0.35	IXFH20N60-ND	9.56 8.65 7.55	IXFH20N60
	600	26	0.250	IXFH26N60Q-ND	12.20 11.04 9.64	IXFH26N60Q
	800	7	1.4	IXFH7N80-ND	6.99 6.33 5.62	IXFH7N80
	800	13	0.80	IXFH13N80-ND	10.56 9.56 8.35	IXFH13N80
	800	15	0.60	IXFH15N80-ND	13.92 12.60 11.01	IXFH15N80
	800	15	0.600	IXFH15N80Q-ND	13.92 12.60 11.01	IXFH15N80Q
	800	20	0.420	IXFH20N80Q-ND	15.41 13.95 12.18	IXFH20N80Q
	900	6	1.8	IXFH6N90-ND	8.11 7.34 6.51	IXFH6N90
	1000	6	2.0	IXFH6N100-ND	7.48 6.77 5.91	IXFH6N100
	1000	10	1.2	IXFH10N100-ND	13.38 12.11 10.57	IXFH10N100
	1000	12	1.05	IXFH12N100-ND	14.11 12.77 11.16	IXFH12N100
24	70	110	0.006	IXFK110N07-ND	17.85 14.88 13.39	IXFK110N07
	100	180	0.008	IXFK180N10-ND	24.45 20.38 16.30	IXFK180N10
	200	90	0.023	IXFK90N20-ND	16.61 15.03 13.45	IXFK90N20
	200	120	0.017	IXFK120N20-ND	25.68 21.40 17.12	IXFK120N20
	300	73	0.045	IXFK73N30-ND	24.48 20.40 16.32	IXFK73N30
	500	48	0.10	IXFK48N50-ND	26.94 22.45 17.96	IXFK48N50
	500	55	0.09	IXFK55N50-ND	33.48 27.90 22.32	IXFK55N50
	600	36	0.180	IXFK36N60-ND	26.49 22.08 17.66	IXFK36N60
	600	44	0.130	IXFK44N60-ND	28.98 24.15 19.32	IXFK44N60
	800	27	0.300	IXFK27N80-ND	30.09 25.08 22.57	IXFK27N80
	800	34	0.240	IXFK34N80-ND	30.87 25.73 20.58	IXFK34N80
	1000	24	0.390	IXFK24N100-ND	33.87 28.23 22.58	IXFK24N100
25	200	120	0.017	IXFK120N20-ND	16.63 15.05 13.15	IXFK120N20
	500	55	0.080	IXFK55N50-ND	23.81 21.55 18.82	IXFK55N50
	1000	15	0.70	IXFK15N100-ND	14.99 13.57 11.85	IXFK15N100
<b>MOSFETs — N-Channel Enhancement Mode with Fast Intrinsic Diode — RoHS Compliant</b>						
24	500	46	0.16	IXTK46N50L-ND	50.07 41.73 33.38	IXTK46N50L
	600	64	0.096	IXFK64N60P-ND	21.96 18.30 14.64	IXFK64N60P
25	500	64	0.085	IXFX64N50P-ND	16.89 14.08 11.26	IXFX64N50P
	500	80	0.065	IXFX80N50P-ND	22.77 18.98 12.60	IXFX80N50P
	600	48	0.135	IXFX48N60P-ND	16.89 14.08 11.26	IXFX48N60P
	600	64	0.096	IXFX64N60P-ND	22.20 18.50 14.80	IXFX64N60P
26	500	44	0.14	IXFK44N50P-ND	11.67 9.73 7.78	IXFK44N50P
	500	64	0.085	IXFK64N50P-ND	16.23 13.53 10.82	IXFK64N50P
	500	80	0.065	IXFK80N50P-ND	22.08 18.40 14.72	IXFK80N50P
	600	36	0.19	IXFK36N60P-ND	11.67 9.73 7.78	IXFK36N60P
	600	48	0.135	IXFK48N60P-ND	16.23 13.53 10.82	IXFK48N60P
27	500	12	0.5	IXFP12N50P-ND		